

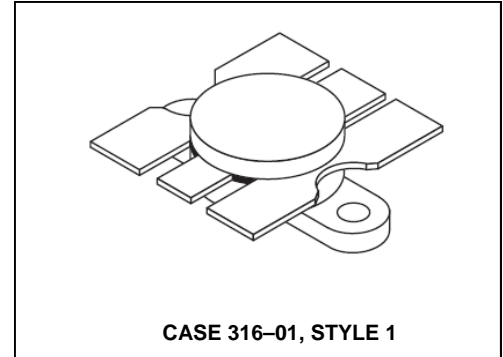
The RF Line NPN Silicon Power Transistor 60W, 225 to 400MHz, 28V

M/A-COM Products
Released - Rev. 07.07

Designed primarily for wideband large-signal output amplifier stages in the 225 to 400 MHz frequency range.

- Guaranteed performance in 225 to 400 MHz broadband amplifier @ 28 Vdc
Output power = 60 W over 225 to 400 MHz band
Minimum gain = 7.8 dB @ 400 MHz
- Built-in matching network for broadband operation using double match technique
- 100% tested for load mismatch at all phase angles with 30:1 VSWR
- Gold metallization system for high reliability applications

Product Image



MAXIMUM RATINGS*

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	33	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ (1) Derate above 25°C	P_D	146 0.83	Watts W°C
Storage Temperature Range	T_{stg}	-65 to +200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.2	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS* ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 50 \text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	33	—	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 50 \text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 5.0 \text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	2.0	mAdc

NOTE:

1. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as RF amplifiers.

(continued)

* Indicates JEDEC Registered Data.

The RF Line NPN Silicon Power Transistor 60W, 225 to 400MHz, 28V

M/A-COM Products
Released - Rev. 07.07

ELECTRICAL CHARACTERISTICS* — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

ON CHARACTERISTICS

DC Current Gain ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	10	—	100	—
---	----------	----	---	-----	---

DYNAMIC CHARACTERISTICS

Output Capacitance ($V_{CB} = 28 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{ob}	—	67	75	pF
---	----------	---	----	----	----

BROADBAND FUNCTIONAL TESTS (Figure 6)

Common-Emitter Amplifier Power Gain ($V_{CC} = 28 \text{ Vdc}$, $P_{out} = 60 \text{ W}$, $f = 225\text{--}400 \text{ MHz}$)	G_{PE}	7.8	8.5	—	dB
Electrical Ruggedness ($P_{out} = 60 \text{ W}$, $V_{CC} = 28 \text{ Vdc}$, $f = 400 \text{ MHz}$, VSWR 30:1 all phase angles)	ψ	No Degradation in Output Power			—

NARROW BAND FUNCTIONAL TESTS (Figure 1)

Common-Emitter Amplifier Power Gain ($V_{CC} = 28 \text{ Vdc}$, $P_{out} = 60 \text{ W}$, $f = 400 \text{ MHz}$)	G_{PE}	7.8	10	—	dB
Collector Efficiency ($V_{CC} = 28 \text{ Vdc}$, $P_{out} = 60 \text{ W}$, $f = 400 \text{ MHz}$)	η	55	—	—	%

* Indicates JEDEC Registered Data.

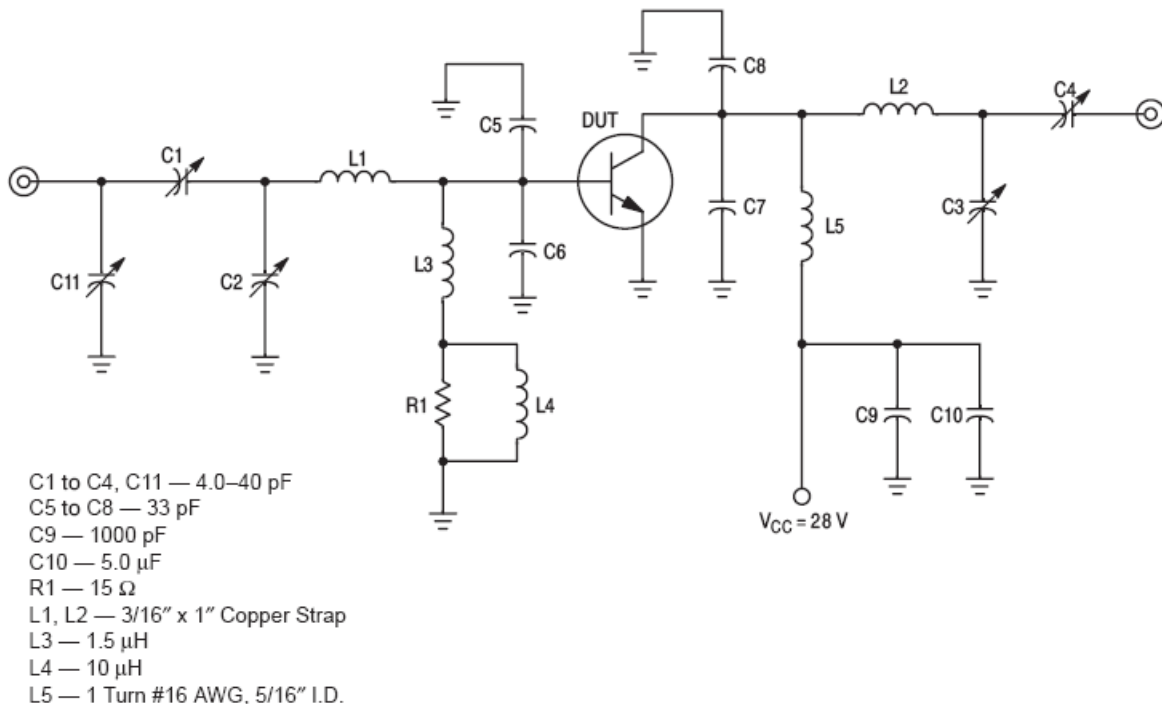


Figure 1. 400 MHz Test Amplifier (Narrow Band)

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

• **North America** Tel: 800.366.2266 / Fax: 978.366.2266
 • **Europe** Tel: 44.1908.574.200 / Fax: 44.1908.574.300
 • **Asia/Pacific** Tel: 81.44.844.8296 / Fax: 81.44.844.8298

Visit www.macomtech.com for additional data sheets and product information.

M/A-COM Technology Solutions Inc. and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.

NARROW BAND DATA

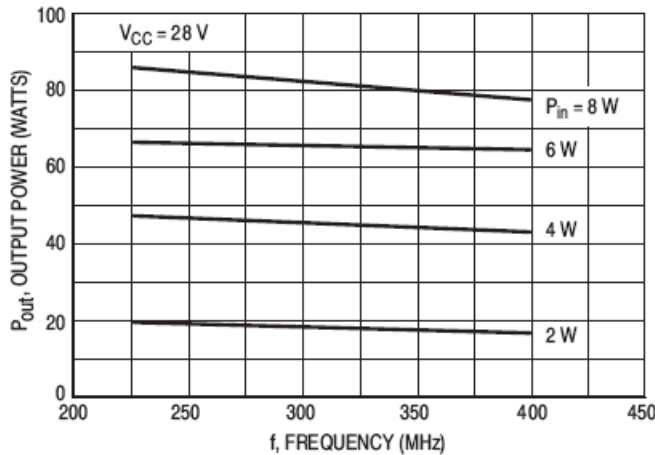


Figure 2. P_{out} versus Frequency

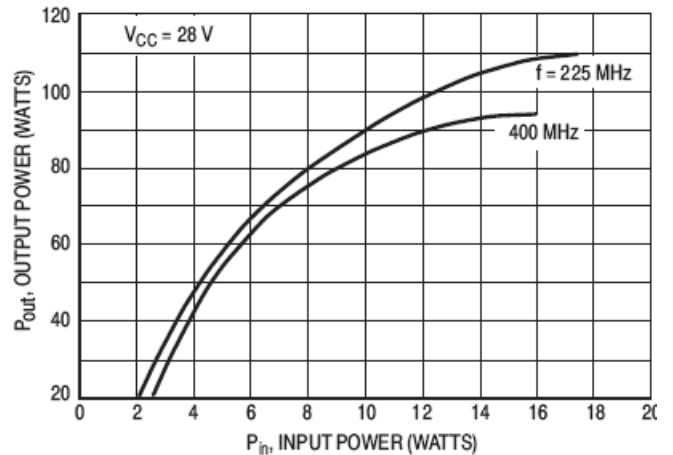


Figure 3. Output Power versus Input Power

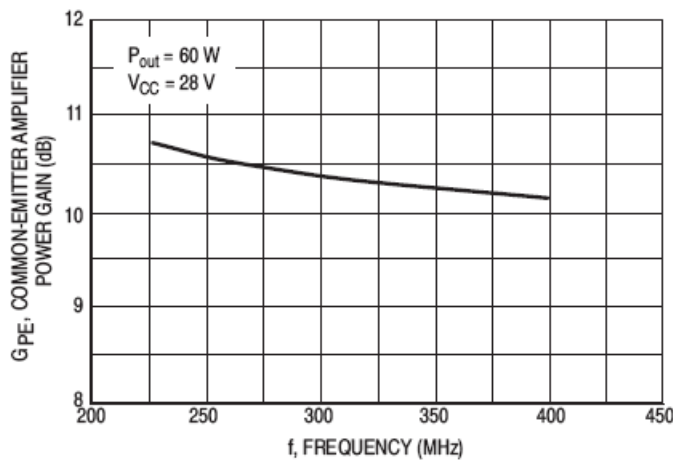


Figure 4. Power Gain versus Frequency

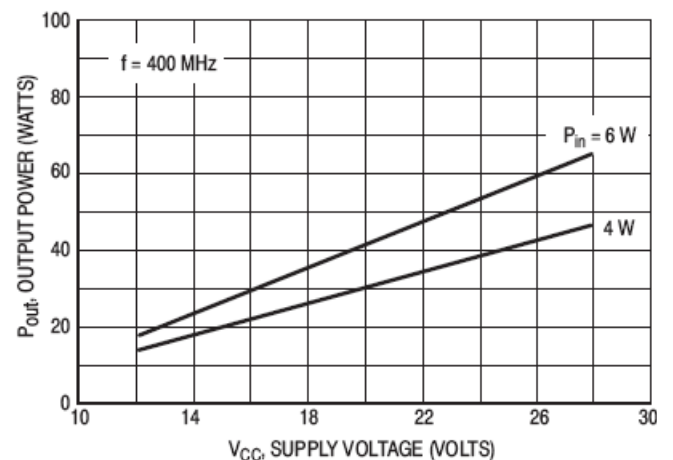


Figure 5. Output Power versus Supply Voltage

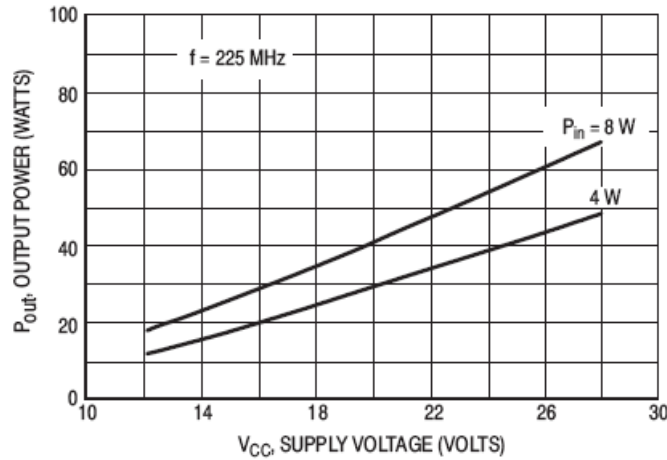
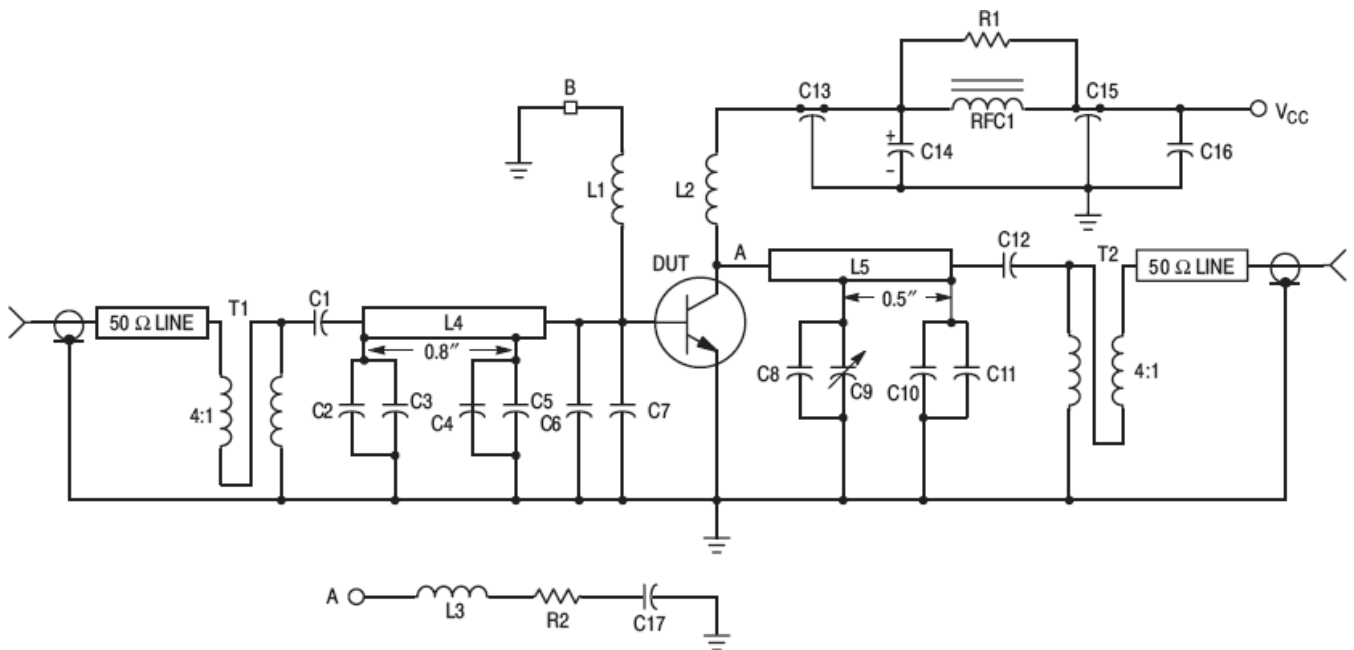


Figure 6. Output Power versus Supply Voltage



- C1 — 68 pF
- C2, C4, C8, C10 — 27 pF
- C3, C5, C11 — 10 pF
- C6, C7 — 51 pF
- C9 — 1.0–10 pF JOHANSON
- C12 — 100 pF
- C13, C15 — 680 pF
- C14, C16 — 1.0 μF, 35 V Tantalum
- C17 — 0.1 μF, ERIE Red Cap

- RFC1 — Ferrite Bead Choke, Ferroxcube VK200 19/4B
- B — Ferroxcube 56-590-65/4B Ferrite Bead
- T1, T2 — 25 Ohms (UT25) Miniature Coaxial Cable, 1 turn
- R1 — 11 Ω, 1.0 W
- R2 — 20 Ω, 1/4 W
- L1 — 10 Turns, #22 AWG, 1/8" I.D.
- L2 — 4 Turns, #16 AWG, 1/4" I.D.
- L3 — 6 Turns, #24 AWG, 1/8" I.D.
- L4, L5 — 1" x 0.25" Microstrip Line
- Board Material 0.031" Thick Teflon-Fiberglass

Figure 7. 225 to 400 MHz Broadband Test Circuit Schematic

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.
PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

- **North America** Tel: 800.366.2266 / Fax: 978.366.2266
 - **Europe** Tel: 44.1908.574.200 / Fax: 44.1908.574.300
 - **Asia/Pacific** Tel: 81.44.844.8296 / Fax: 81.44.844.8298
- Visit www.macomtech.com for additional data sheets and product information.

M/A-COM Technology Solutions Inc. and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.

BROADBAND DATA (Circuit, Figure 7)

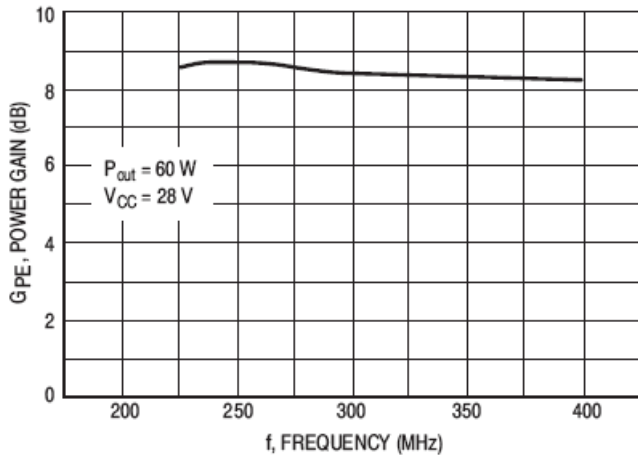


Figure 8. Power Gain versus Frequency

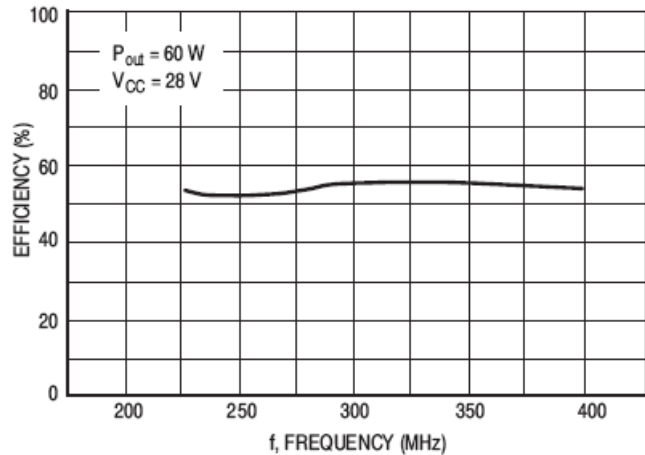


Figure 9. Efficiency versus Frequency

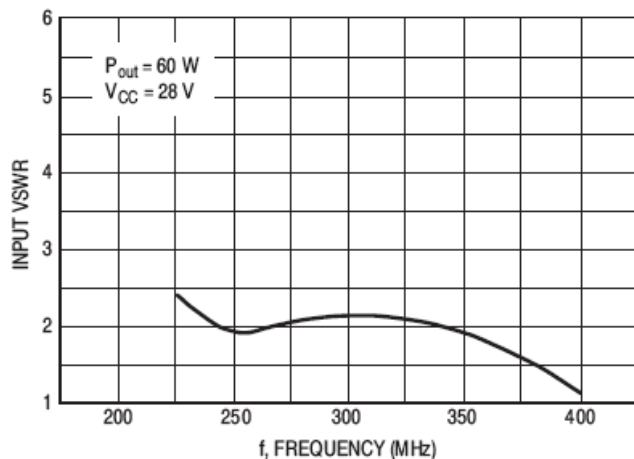


Figure 10. Input VSWR versus Frequency

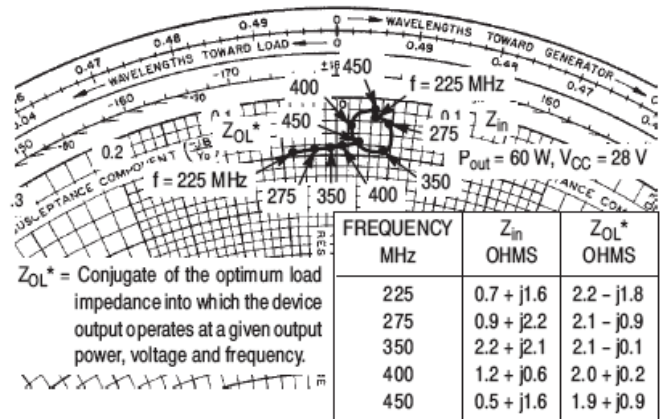


Figure 11. Series Equivalent Input-Output Impedance

PACKAGE DIMENSIONS

